	U	1	D	ocument	ID	Issue Date	Pages	Title	Current OR	Curre
1	П	Ø	US	6369490	B1	20020409	9	Surface acoustic wave device having bump electrodes	310/364	310/3
2	Г	Ø	US	5746930	Α	19980505	11	Method and structure for forming an array of thermal	216/87	216/10 216/5
3	П	7	1			19950808	5	Radiation detector having a pyroelectric ceramic	250/338.1	250/33 501/13
4	n		1	6064120		20000516	10	Apparatus and method for face-to-face connection of a	257/780	257/78 257/E2
5	П	ŧ	i			19991116	15	Electrochemical device	429/188	429/23 429/30
6	П		ļ	5896081		19990420	11	Resistance temperature detector (RTD) formed with a	338/22R	
7	Г	•				19980707	12	Transparent and opaque metal-semiconductor-metal	257/749	257/44 257/45
8	П	:	1			20001024	10	Flip-chip type semiconductor device having	<u>:</u>	257/73 257/73
9	Г	•	ļ			19991130	11	Method of manufacture of surface acoustic wave device	29/25.35	310/31
10	Γ	•	ì	6028011		20000222	16	Method of forming electric pad of semiconductor device	438/745	257/E2 438/61
11	Г		ì			19971216	17	Surface acoustic wave devices having a guard layer	333/193	310/31 310/34
12	П		}	4692653		19870908	:	Acoustic transducers utilizing ZnO thin film	310/334	310/36 310/36
13	Γ		•			19920428	11	Method for forming a bump electrode for a		148/DI 257/69
14	П					19810331	4	Quartz crystal vibrator using Ni-Ag or Cr-Ni-Ag	310/364	
15	Г	F	បន	4736128	A	19880405	6	Surface acoustic wave device		310/31 310/34
16			បន	5325012	A	19940628	15	Bonded type piezoelectric	310/364	228/1

	U	1	D	ocument 3	Œ	Issue Date	Pages	Title	Current OR	Current
11	Г	R	υs	5699027	A	19971216	17	Surface acoustic wave devices having a guard layer	333/193	310/313 310/344
12	Г	R	US	4692653	Α	19870908	10	Acoustic transducers utilizing ZnO thin film	310/334	310/364 310/365
13	Г	P	US	5108950	A	19920428	11	Method for forming a bump electrode for a	438/614	148/DIG 257/690
14	Г	V	υs	4259607	A	19810331	4	Quartz crystal vibrator using Ni-Ag or Cr-Ni-Ag	310/364	
15	Г	M.	1	4736128			6	Surface acoustic wave device	310/313R	310/313 310/348
16		17.:	1	5325012			15	Bonded type piezoelectric apparatus, method for	310/364	228/121 228/124
17	г		Į.		5		14	Electrochemical device	429/304	429/33
18	Г		i	07187894			4	Ferroelectric thin film for substrate material for	and the confidence of the conf	and the contribute of both of both of both on the contribute
19	Г	P	US	5134460	A	19920728	10	Aluminum bump, reworkable bump, and titanium nitride	257/737	257/733 257/771
20	r	Þ	JΡ	54128280	А	19791004	3	RESIN-SEALED SEMICONDUCTOR DEVICE		257/766 257/771
21	Г	Þ	US	4330182	A	19820518	11	Method of forming semiconducting materials and	257/56	136/249 136/258
22	Г	7	US	5591321	A	19970107	•		205/787	204/401 204/412
23	г	7	បទ	6404110	В1	20020611		Surface acoustic wave element having a bump	310/364	310/313
24	П	M		6326052				girl to whit to with the part they are through those part through those part through those part through those part through the part to	427/79	204/192 29/25.4
25	г	V	JР	60116168	A	19850622		WIRING ELECTRODE OF EQUAL MAGNIFICATION SENSOR		257/459 257/E31